



PTO/SB/08a/b (08-03)

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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete If Known	
				Application Number	10/787,121
				Filing Date	February 27, 2004
				First Named Inventor	John T. Moore
				Art Unit	2812
				Examiner Name	Not Yet Assigned
Sheet	1	of	3	Attorney Docket Number	M4065.0564/P564-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
W	A	US 2004/0035401	2/2004	Ramachandran et al.	
	B	US 2003/0212724	11/2003	Ovshinsky et al.	
	C	US 2003/0048744	3/2003	Ovshinsky et al.	
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NON PATENT LITERATURE DOCUMENTS			
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A. Jay Tson 5/4/05

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		Number-Kind Code ² (if known)			
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W	AB	6,084,796	07/04/2000	Kozicki et al. **	
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)			
	BA	WO 02/21542	03/14/2002	Kozicki et al. **	
	BB	WO 00/48196	08/17/2000	Kozicki et al. **	
	BC	WO 97/48032	12/18/1997	Kozicki et al. **	
	BD	WO 99/28914	06/10/1999	Kozicki et al. **	

Examiner Signature	H-Jey TSA	Date Considered	5/4/05
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		Filing Date	March 1, 2004
		First Named Inventor	John T. Moore
		Group Art Unit	Not Yet Assigned
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Sheet	2	of	8

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume/issue number(s), publisher, city and/or country where published.	T ²
	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853. **	
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